

- Advanced Process Technology
- Ultra Low On-Resistance
- Dynamic dv/dt Rating
- 175°C Operating Temperature
- Fast Switching
- Fully Avalanche Rated

Description

Seventh Generation HEXFET® Power MOSFETs from International Rectifier utilize advanced processing techniques to achieve extremely low on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in a wide variety of applications.

The D²Pak is a surface mount power package capable of accommodating die sizes up to HEX-4. It provides the highest power capability and the lowest possible on-resistance in any existing surface mount package. The D²Pak is suitable for high current applications because of its low internal connection resistance and can dissipate up to 2.0W in a typical surface mount application.

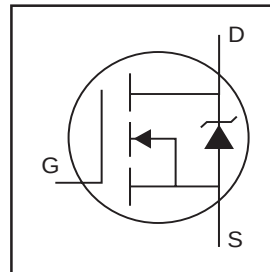
The through-hole version (IRF1404L) is available for low-profile applications.

Absolute Maximum Ratings

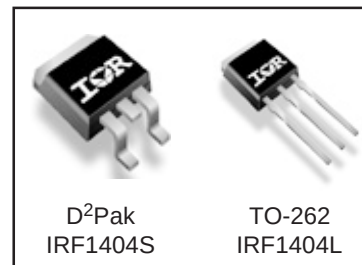
	Parameter	Max.	Units
I_D @ $T_C = 25^\circ\text{C}$	Continuous Drain Current, V_{GS} @ 10V⑦	162⑥	A
I_D @ $T_C = 100^\circ\text{C}$	Continuous Drain Current, V_{GS} @ 10V⑦	115⑥	
I_{DM}	Pulsed Drain Current ①⑦	650	
P_D @ $T_A = 25^\circ\text{C}$	Power Dissipation	3.8	W
P_D @ $T_C = 25^\circ\text{C}$	Power Dissipation	200	W
	Linear Derating Factor	1.3	W/°C
V_{GS}	Gate-to-Source Voltage	± 20	V
E_{AS}	Single Pulse Avalanche Energy⑦	519	mJ
I_{AR}	Avalanche Current①	95	A
E_{AR}	Repetitive Avalanche Energy①	20	mJ
dv/dt	Peak Diode Recovery dv/dt ③⑦	5.0	V/ns
T_J	Operating Junction and	-55 to +175	°C
T_{STG}	Storage Temperature Range	-55 to +175	
	Soldering Temperature, for 10 seconds	300 (1.6mm from case)	

Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	0.75	°C/W
$R_{\theta JA}$	Junction-to-Ambient (PCB mounted, steady-state)*	—	40	



$V_{DSS} = 40\text{V}$
$R_{DS(on)} = 0.004\Omega$
$I_D = 162\text{A}⑥$



D²Pak
IRF1404S

TO-262
IRF1404L

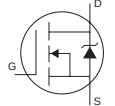
IRF1404S/L

International
IR Rectifier

Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	40	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.036	—	V/ $^\circ\text{C}$	Reference to 25°C , $I_D = 1mA$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	0.0035	0.004	Ω	$V_{GS} = 10V, I_D = 95A$ ④
$V_{GS(th)}$	Gate Threshold Voltage	2.0	—	4.0	V	$V_{DS} = 10V, I_D = 250\mu A$
g_{fs}	Forward Transconductance	106	—	—	S	$V_{DS} = 25V, I_D = 60A$ ⑦
I_{DSS}	Drain-to-Source Leakage Current	—	—	20	μA	$V_{DS} = 40V, V_{GS} = 0V$
		—	—	250		$V_{DS} = 32V, V_{GS} = 0V, T_J = 150^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	200	nA	$V_{GS} = 20V$
	Gate-to-Source Reverse Leakage	—	—	-200		$V_{GS} = -20V$
Q_g	Total Gate Charge	—	160	200	nC	$I_D = 95A$
Q_{gs}	Gate-to-Source Charge	—	35	—		$V_{DS} = 32V$
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	42	60		$V_{GS} = 10V$ ④ ⑦
$t_{d(on)}$	Turn-On Delay Time	—	17	—	ns	$V_{DD} = 20V$
t_r	Rise Time	—	140	—		$I_D = 95A$
$t_{d(off)}$	Turn-Off Delay Time	—	72	—		$R_G = 2.5\Omega$
t_f	Fall Time	—	26	—		$R_D = 0.21\Omega$ ④ ⑦
L_S	Internal Source Inductance	—	7.5	—	nH	Between lead, and center of die contact
C_{iss}	Input Capacitance	—	7360	—	pF	$V_{GS} = 0V$
C_{oss}	Output Capacitance	—	1680	—		$V_{DS} = 25V$
C_{rss}	Reverse Transfer Capacitance	—	240	—		$f = 1.0MHz$, See Fig. 5 ⑦
C_{oss}	Output Capacitance	—	6630	—		$V_{GS} = 0V, V_{DS} = 1.0V, f = 1.0MHz$
C_{oss}	Output Capacitance	—	1490	—		$V_{GS} = 0V, V_{DS} = 32V, f = 1.0MHz$
$C_{oss \text{ eff.}}$	Effective Output Capacitance ⑤ ⑦	—	1540	—		$V_{GS} = 0V, V_{DS} = 0V \text{ to } 32V$

Source-Drain Ratings and Characteristics

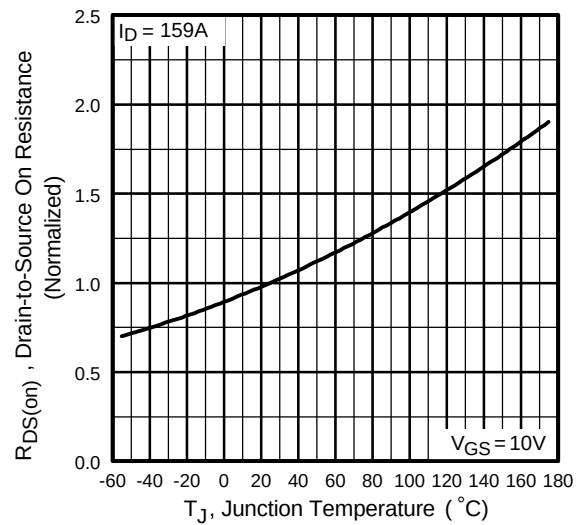
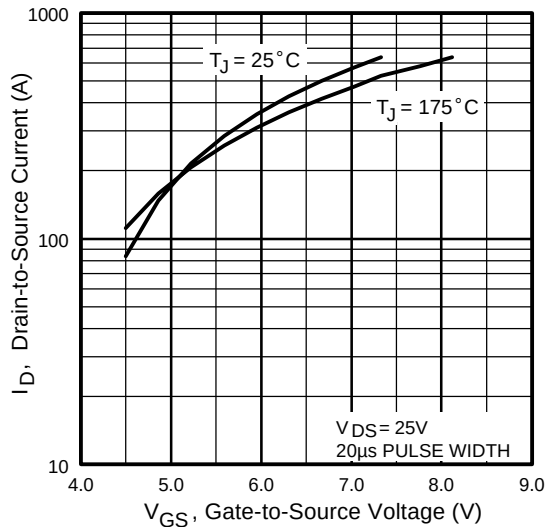
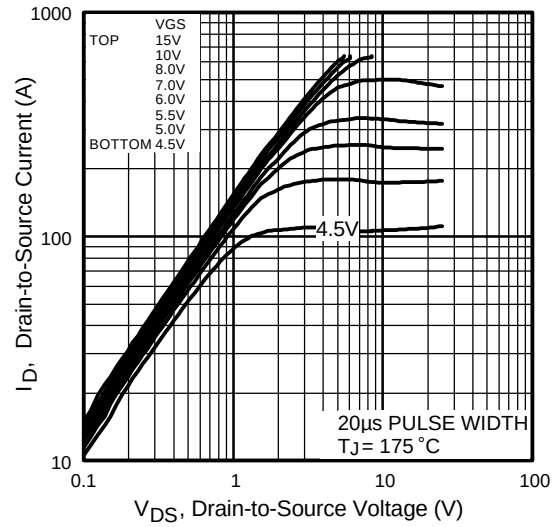
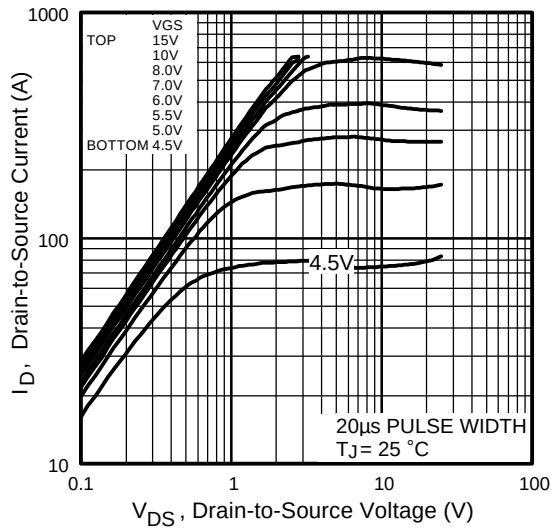
	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	162	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	650		
V_{SD}	Diode Forward Voltage	—	—	1.3	V	$T_J = 25^\circ\text{C}, I_S = 95A, V_{GS} = 0V$ ④
t_{rr}	Reverse Recovery Time	—	71	110	ns	$T_J = 25^\circ\text{C}, I_F = 95A$
Q_{rr}	Reverse Recovery Charge	—	180	270	nC	$di/dt = 100A/\mu s$ ④ ⑦
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by $L_S + L_D$)				

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)
- ② Starting $T_J = 25^\circ\text{C}$, $L = 0.12mH$, $R_G = 25\Omega$, $I_{AS} = 95A$. (See Figure 12)
- ③ $I_{SD} \leq 95A$, $di/dt \leq 150A/\mu s$, $V_{DD} \leq V_{(BR)DSS}$, $T_J \leq 175^\circ\text{C}$
- ④ Pulse width $\leq 300\mu s$; duty cycle $\leq 2\%$.
- ⑤ $C_{oss \text{ eff.}}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS}
- ⑥ Calculated continuous current based on maximum allowable junction temperature. Package limitation current is 75A
- ⑦ Use IRF1404 data and test conditions.

* When mounted on 1" square PCB (FR-4 or G-10 Material).

For recommended footprint and soldering techniques refer to application note #AN-994.



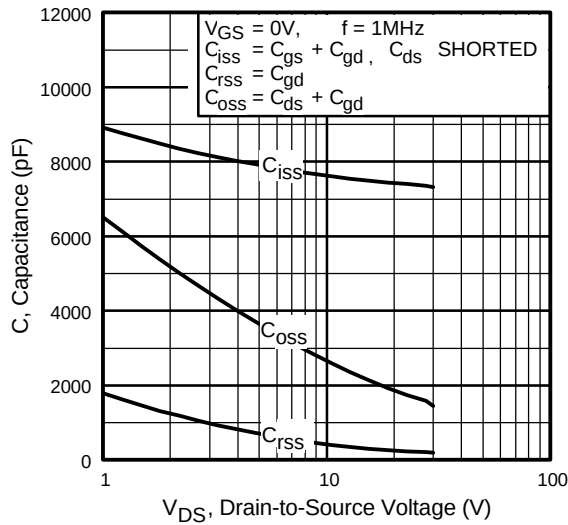


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

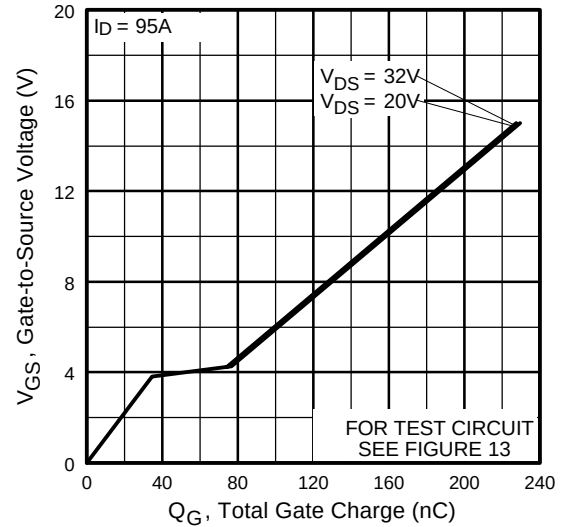


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

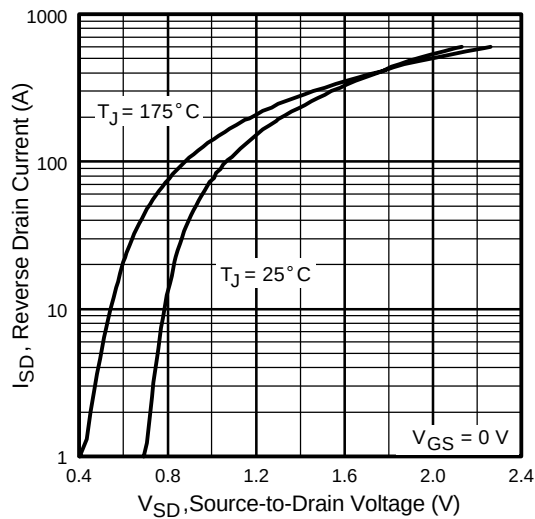


Fig 7. Typical Source-Drain Diode Forward Voltage

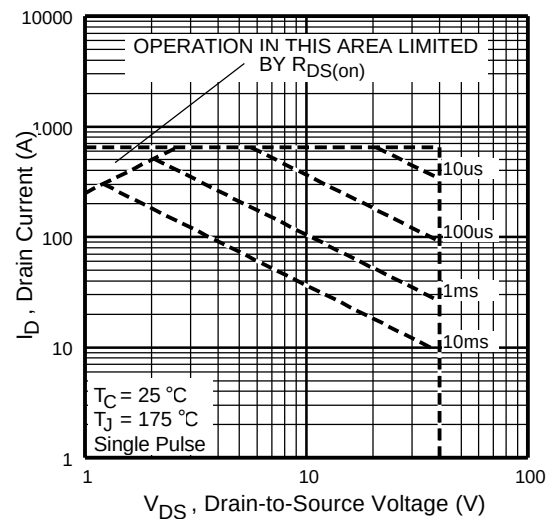


Fig 8. Maximum Safe Operating Area

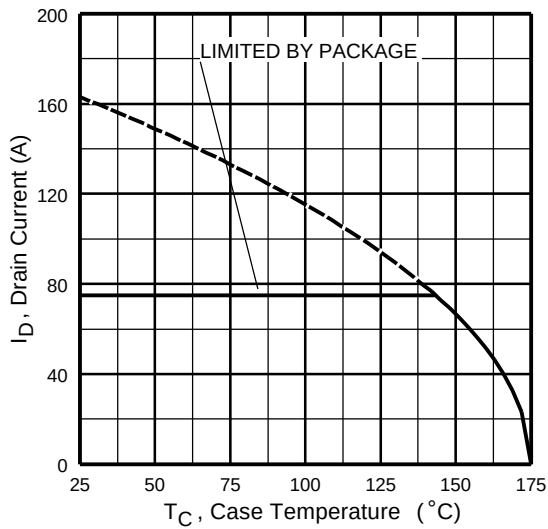


Fig 9. Maximum Drain Current Vs. Case Temperature

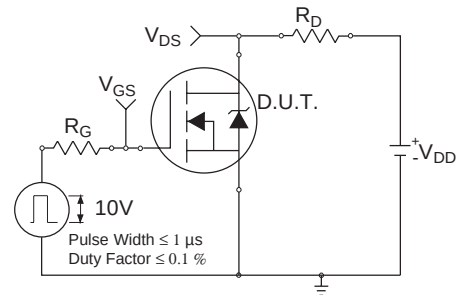


Fig 10a. Switching Time Test Circuit

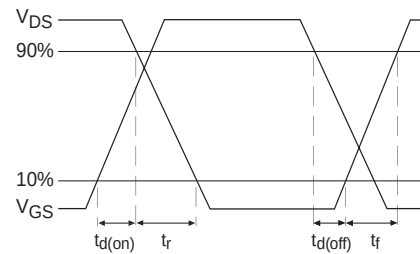


Fig 10b. Switching Time Waveforms

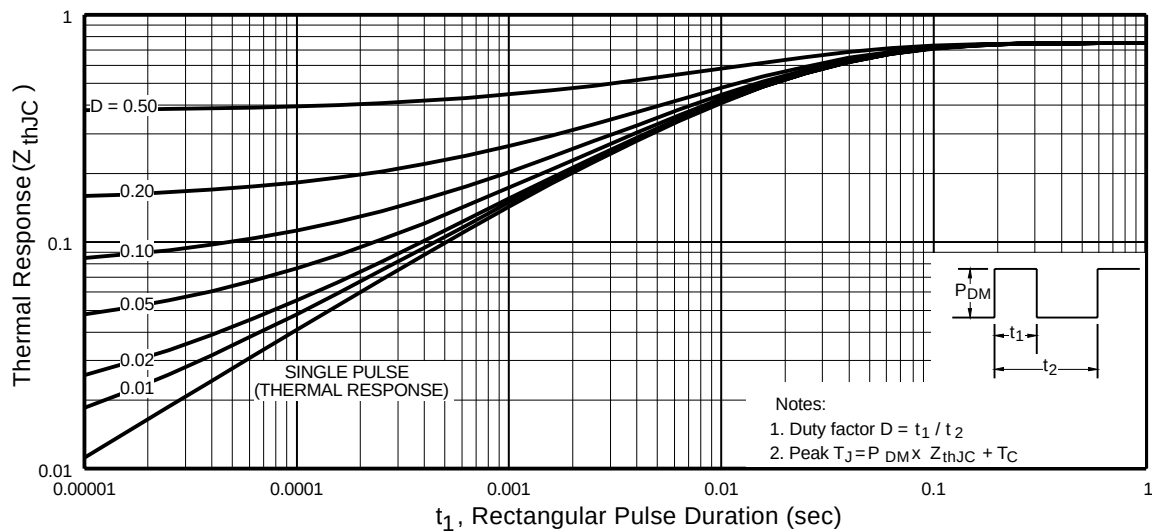


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

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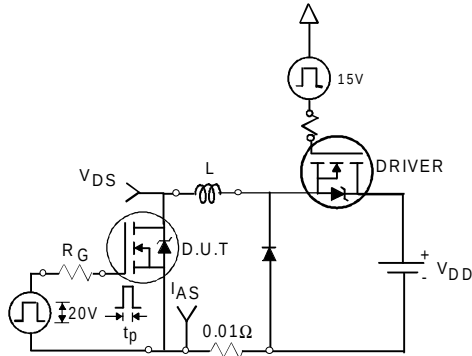


Fig 12a. Unclamped Inductive Test Circuit

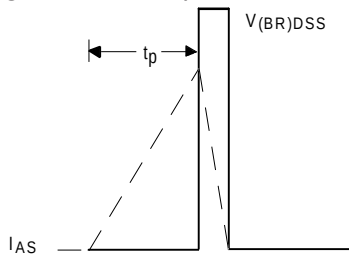


Fig 12b. Unclamped Inductive Waveforms

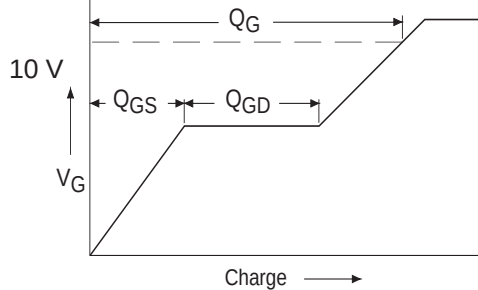


Fig 13a. Basic Gate Charge Waveform

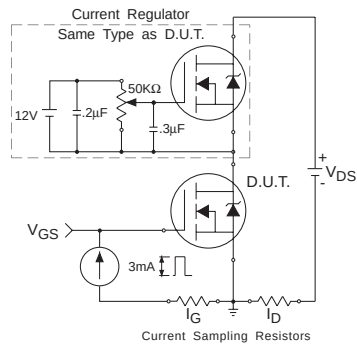


Fig 13b. Gate Charge Test Circuit

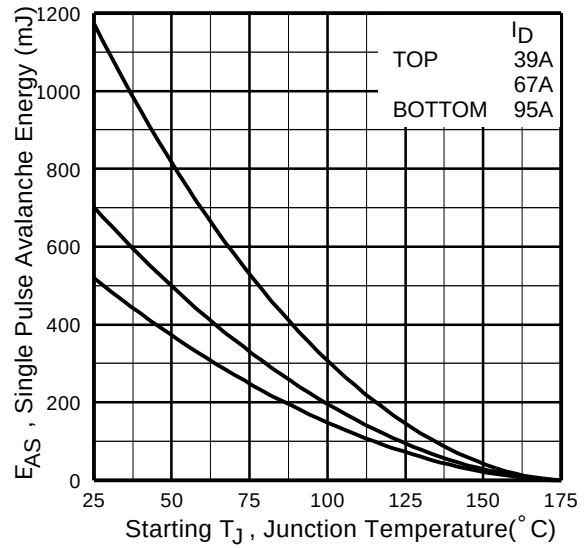


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

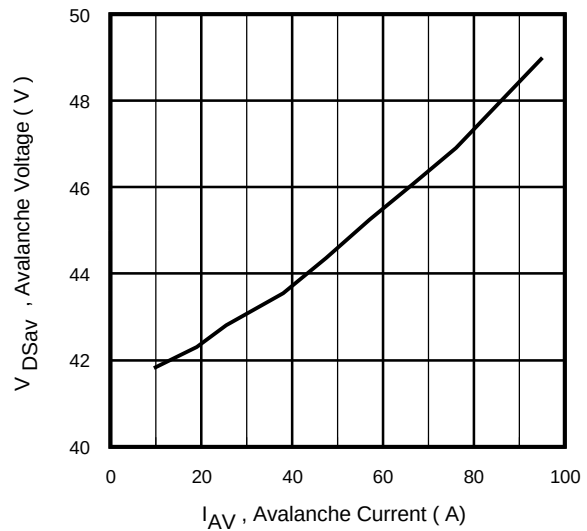
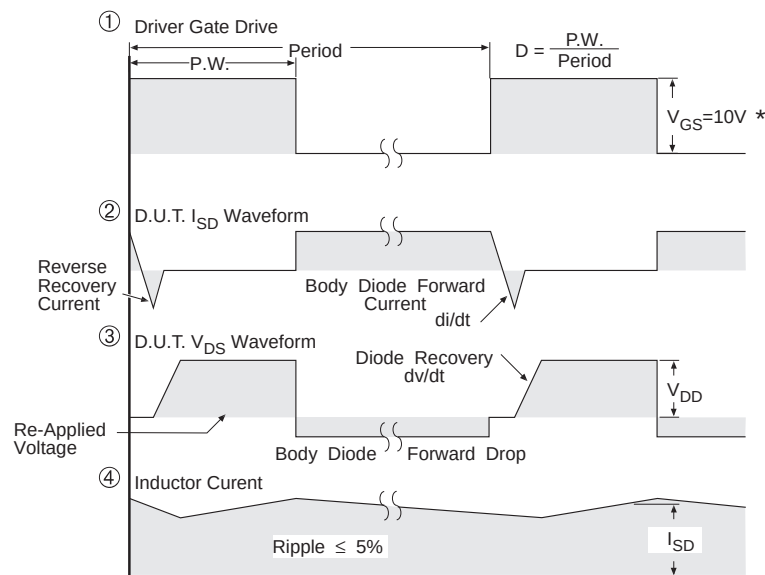
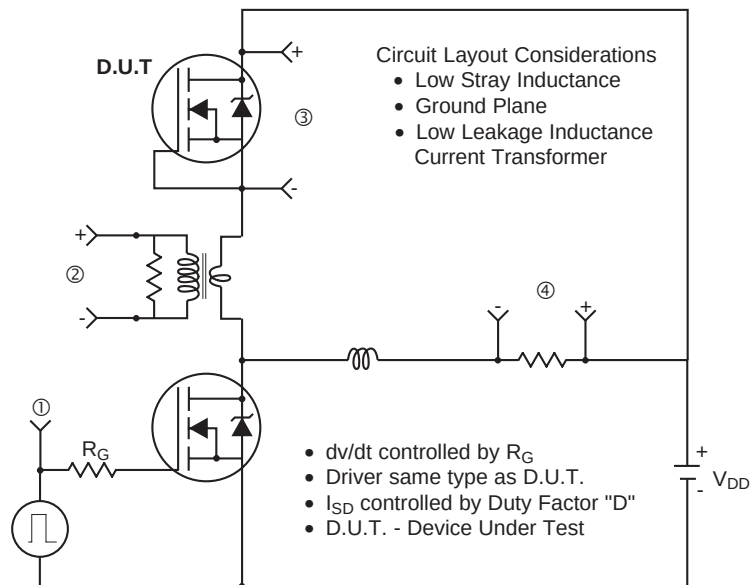


Fig 12d. Typical Drain-to-Source Voltage Vs. Avalanche Current

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Peak Diode Recovery dv/dt Test Circuit



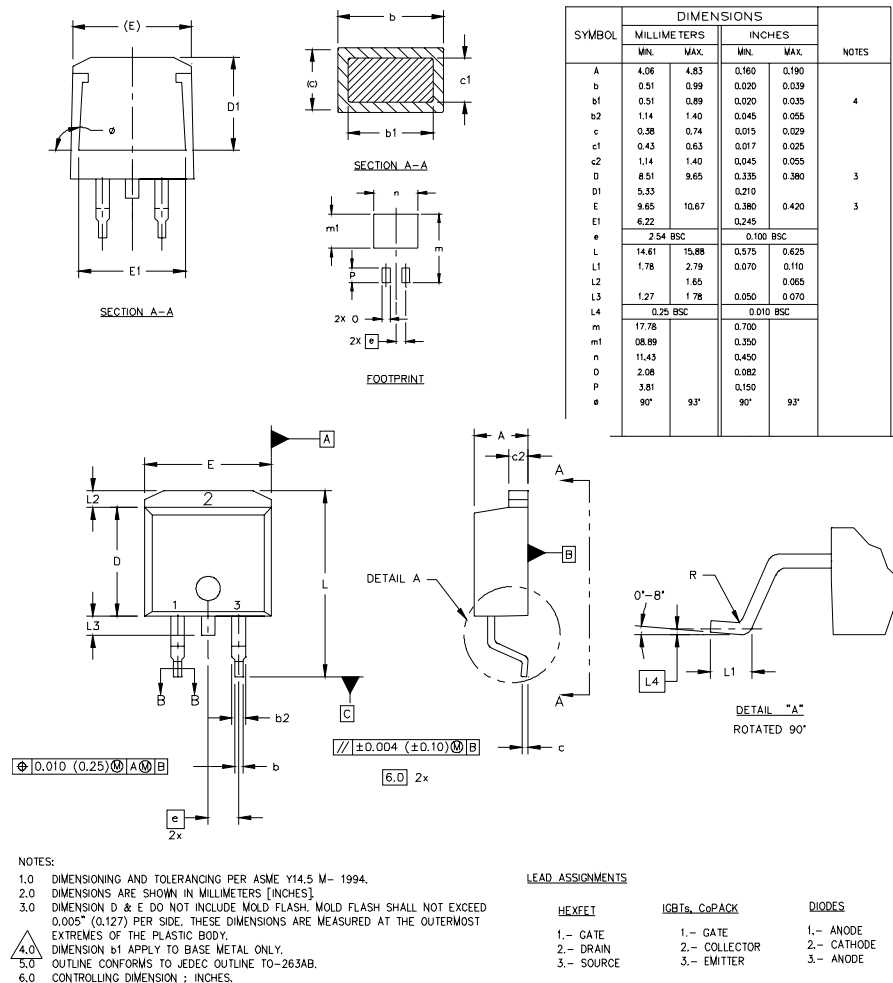
* $V_{GS} = 5V$ for Logic Level Devices

Fig 14. For N-channel HEXFET® Power MOSFETs

IRF1404S/L

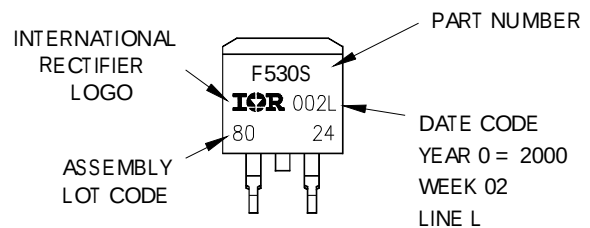
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D²Pak Package Outline



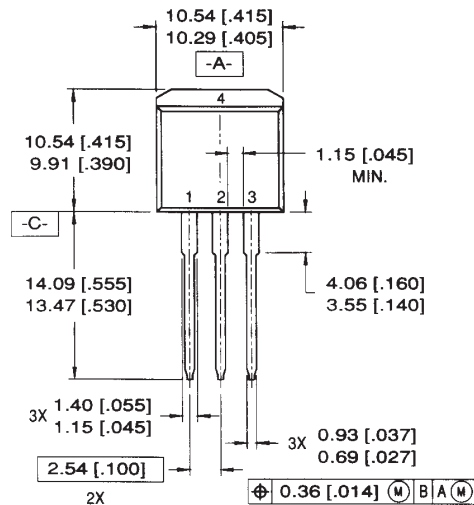
D²Pak Part Marking Information

EXAMPLE: THIS IS AN IRF530S WITH
LOT CODE 8024
ASSEMBLED ON WW02, 2000
IN THE ASSEMBLY LINE "L"



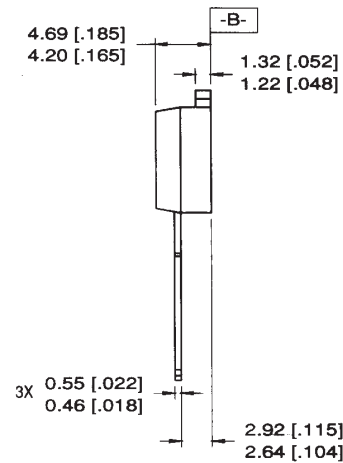
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TO-262 Package Outline



LEAD ASSIGNMENTS

1 = GATE 3 = SOURCE
2 = DRAIN 4 = DRAIN

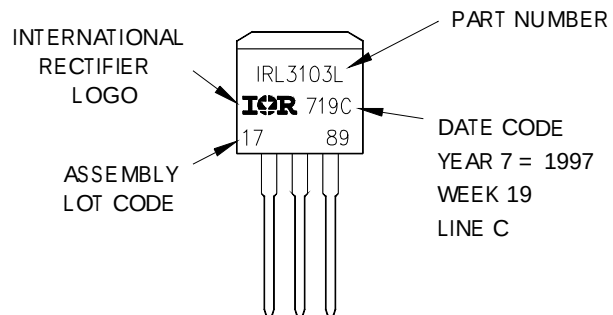


NOTES:

1. DIMENSIONING & TOLERANCING PER ANSI Y14.5M-1982
2. CONTROLLING DIMENSION: INCH.
3. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
4. HEATSINK & LEAD DIMENSIONS DO NOT INCLUDE BURRS.

TO-262 Part Marking Information

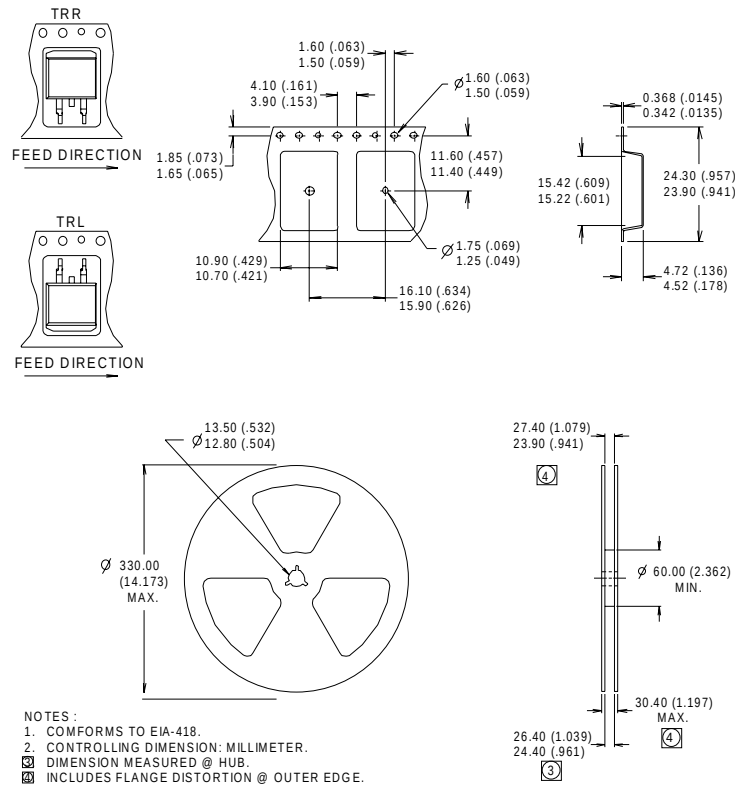
EXAMPLE: THIS IS AN IRL3103L
LOT CODE 1789
ASSEMBLED ON WW 19, 1997
IN THE ASSEMBLY LINE "C"



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D²Pak Tape & Reel Information



Data and specifications subject to change without notice.
This product has been designed and qualified for the Industrial market.
Qualification Standards can be found on IR's Web site.

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